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Kind regards,

Team Nexperia



# PBSS4420D

20 V, 4 A NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 02 — 24 September 2008

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough in Small Signal (BISS) transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5420D.

### 1.2 Features

- Very low collector-emitter saturation resistance
- Ultra low collector-emitter saturation voltage
- 4 A continuous collector current
- Up to 15 A peak current
- High efficiency due to less heat generation

### 1.3 Applications

- Power management functions
- Charging circuits
- DC-to-DC conversion
- MOSFET gate driving
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

### 1.4 Quick reference data

Table 1. Quick reference data

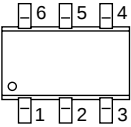
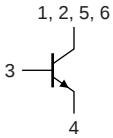
| Symbol      | Parameter                               | Conditions                       | Min   | Typ | Max | Unit       |
|-------------|-----------------------------------------|----------------------------------|-------|-----|-----|------------|
| $V_{CEO}$   | collector-emitter voltage               | open base                        | -     | -   | 20  | V          |
| $I_C$       | collector current                       |                                  | [1] - | -   | 4   | A          |
| $I_{CM}$    | peak collector current                  | single pulse;<br>$t_p \leq 1$ ms | -     | -   | 15  | A          |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = 4$ A;<br>$I_B = 400$ mA   | [2] - | 50  | 70  | m $\Omega$ |

[1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $Al_2O_3$ , standard footprint.

[2] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline                                                                  | Graphic symbol                                                                      |
|-----|-------------|-------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | collector   |  |  |
| 2   | collector   |                                                                                     |                                                                                     |
| 3   | base        |                                                                                     |                                                                                     |
| 4   | emitter     |                                                                                     |                                                                                     |
| 5   | collector   |                                                                                     |                                                                                     |
| 6   | collector   |                                                                                     |                                                                                     |

3. Ordering information

Table 3. Ordering information

| Type number | Package |                                                  |         |
|-------------|---------|--------------------------------------------------|---------|
|             | Name    | Description                                      | Version |
| PBSS4420D   | SC-74   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS4420D   | D4           |

5. Limiting values

Table 5. Limiting values

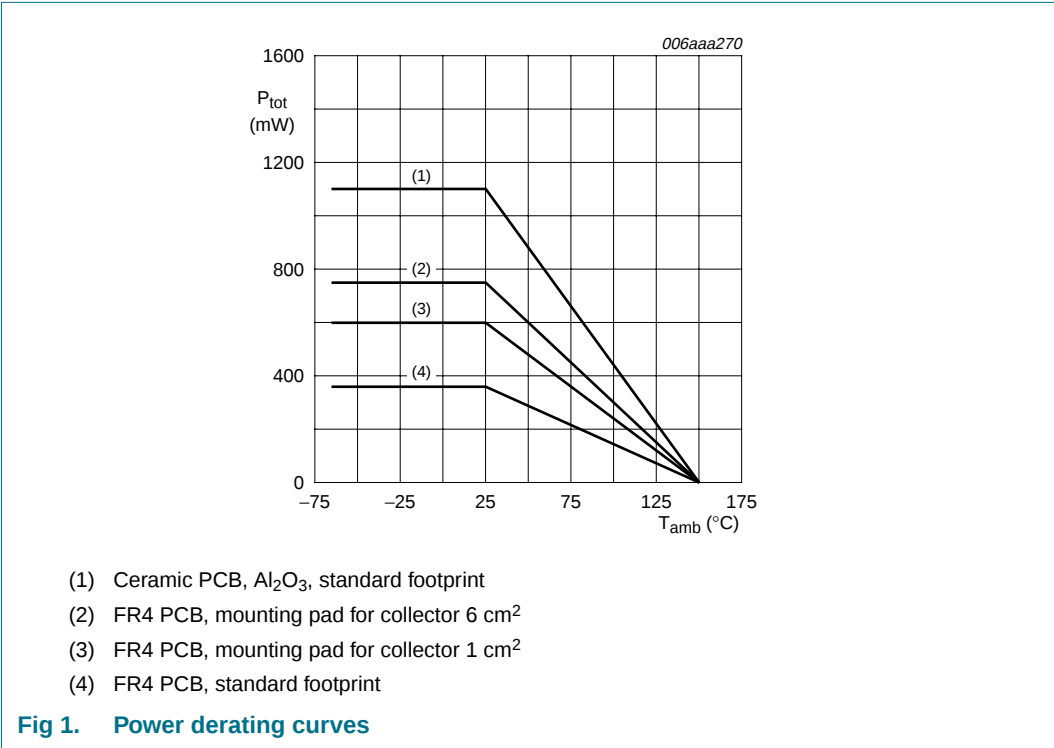
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                             | Min    | Max | Unit |    |
|------------------|---------------------------|----------------------------------------|--------|-----|------|----|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                           | -      | 20  | V    |    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                              | -      | 20  | V    |    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                         | -      | 5   | V    |    |
| I <sub>C</sub>   | collector current         | [1]                                    | -      | 4   | A    |    |
| I <sub>CM</sub>  | peak collector current    | single pulse;<br>t <sub>p</sub> ≤ 1 ms | -      | 15  | A    |    |
| I <sub>B</sub>   | base current              |                                        | -      | 0.8 | A    |    |
| I <sub>BM</sub>  | peak base current         | single pulse;<br>t <sub>p</sub> ≤ 1 ms | -      | 2   | A    |    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C               | [2]    | -   | 360  | mW |
|                  |                           |                                        | [3]    | -   | 600  | mW |
|                  |                           |                                        | [4]    | -   | 750  | mW |
|                  |                           |                                        | [1]    | -   | 1.1  | W  |
|                  |                           |                                        | [2][5] | -   | 2.5  | W  |

**Table 5. Limiting values ...continued**  
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol    | Parameter            | Conditions | Min | Max  | Unit |
|-----------|----------------------|------------|-----|------|------|
| $T_j$     | junction temperature |            | -   | 150  | °C   |
| $T_{amb}$ | ambient temperature  |            | -65 | +150 | °C   |
| $T_{stg}$ | storage temperature  |            | -65 | +150 | °C   |

- [1] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Operated under pulsed conditions: Duty cycle  $\delta \leq 10\%$  and pulse width  $t_p \leq 10\text{ ms}$ .

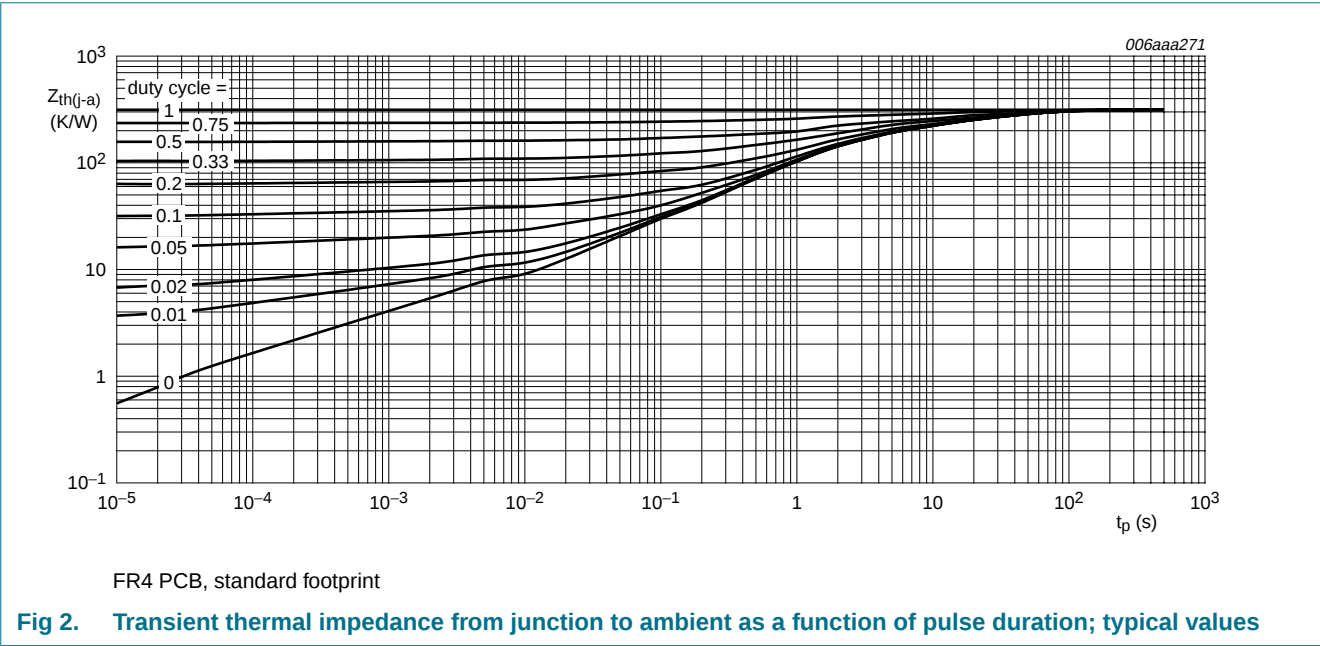


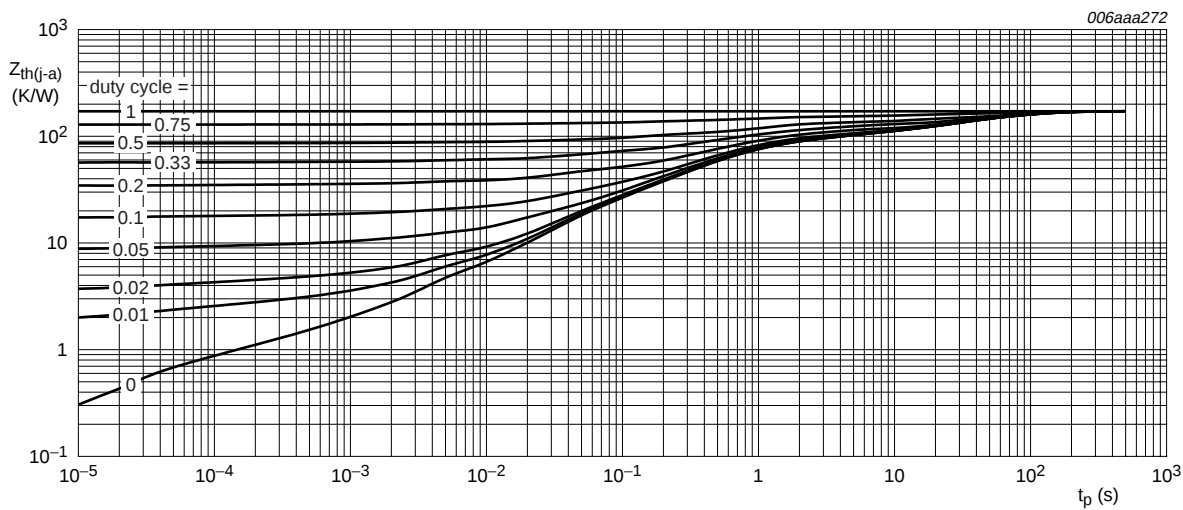
6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter                                        | Conditions  | Min    | Typ | Max | Unit    |
|-----------------------|--------------------------------------------------|-------------|--------|-----|-----|---------|
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | in free air | [1]    | -   | -   | 350 K/W |
|                       |                                                  |             | [2]    | -   | -   | 208 K/W |
|                       |                                                  |             | [3]    | -   | -   | 160 K/W |
|                       |                                                  |             | [4]    | -   | -   | 113 K/W |
|                       |                                                  |             | [1][5] | -   | -   | 50 K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             | -      | -   | 45  | K/W     |

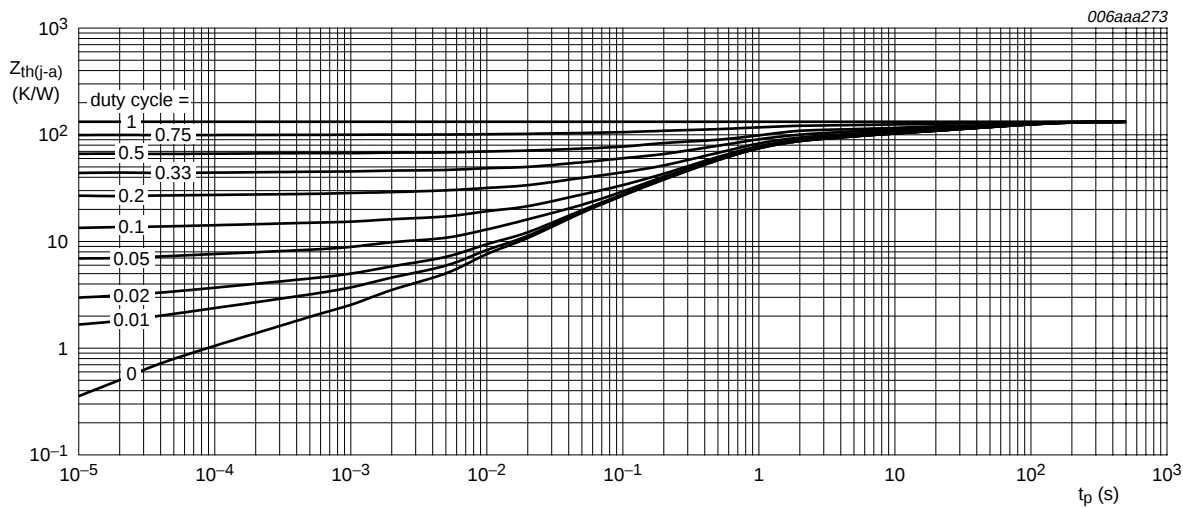
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Operated under pulsed conditions: Duty cycle δ ≤ 10 % and pulse width t<sub>p</sub> ≤ 10 ms.





FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

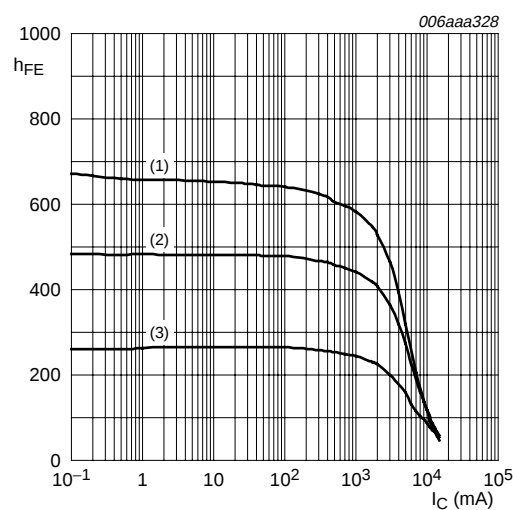
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

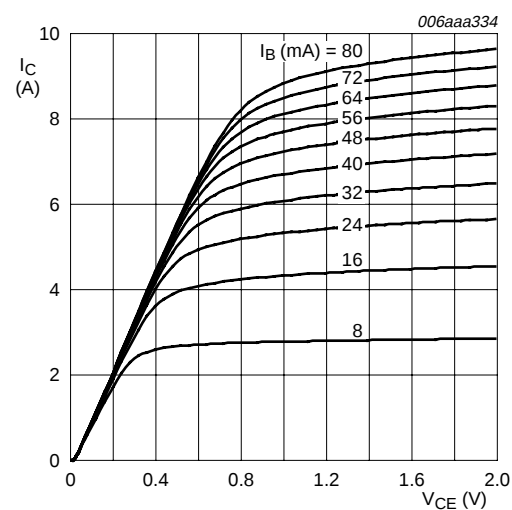
| Symbol      | Parameter                               | Conditions                                                                                     | Min | Typ  | Max  | Unit          |
|-------------|-----------------------------------------|------------------------------------------------------------------------------------------------|-----|------|------|---------------|
| $I_{CBO}$   | collector-base cut-off current          | $V_{CB} = 20\text{ V}; I_E = 0\text{ A}$                                                       | -   | -    | 0.1  | $\mu\text{A}$ |
|             |                                         | $V_{CB} = 20\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$                    | -   | -    | 50   | $\mu\text{A}$ |
| $I_{CES}$   | collector-emitter cut-off current       | $V_{CE} = 20\text{ V}; V_{BE} = 0\text{ V}$                                                    | -   | -    | 0.1  | $\mu\text{A}$ |
| $I_{EBO}$   | emitter-base cut-off current            | $V_{EB} = 5\text{ V}; I_C = 0\text{ A}$                                                        | -   | -    | 0.1  | $\mu\text{A}$ |
| $h_{FE}$    | DC current gain                         | $V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$                                                      | 300 | 450  | -    |               |
|             |                                         | $V_{CE} = 2\text{ V}; I_C = 1\text{ A}$ [1]                                                    | 300 | 430  | -    |               |
|             |                                         | $V_{CE} = 2\text{ V}; I_C = 2\text{ A}$ [1]                                                    | 250 | 400  | -    |               |
|             |                                         | $V_{CE} = 2\text{ V}; I_C = 4\text{ A}$ [1]                                                    | 200 | 310  | -    |               |
|             |                                         | $V_{CE} = 2\text{ V}; I_C = 6\text{ A}$ [1]                                                    | 100 | 230  | -    |               |
| $V_{CEsat}$ | collector-emitter saturation voltage    | $I_C = 0.5\text{ A}; I_B = 50\text{ mA}$                                                       | -   | 30   | 50   | mV            |
|             |                                         | $I_C = 1\text{ A}; I_B = 50\text{ mA}$                                                         | -   | 60   | 90   | mV            |
|             |                                         | $I_C = 2\text{ A}; I_B = 200\text{ mA}$                                                        | -   | 110  | 150  | mV            |
|             |                                         | $I_C = 4\text{ A}; I_B = 400\text{ mA}$ [1]                                                    | -   | 200  | 280  | mV            |
|             |                                         | $I_C = 6\text{ A}; I_B = 600\text{ mA}$ [1]                                                    | -   | 300  | 420  | mV            |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = 4\text{ A}; I_B = 400\text{ mA}$ [1]                                                    | -   | 50   | 70   | m $\Omega$    |
| $V_{BEsat}$ | base-emitter saturation voltage         | $I_C = 0.5\text{ A}; I_B = 50\text{ mA}$                                                       | -   | 0.79 | 0.85 | V             |
|             |                                         | $I_C = 1\text{ A}; I_B = 50\text{ mA}$                                                         | -   | 0.81 | 0.9  | V             |
|             |                                         | $I_C = 1\text{ A}; I_B = 100\text{ mA}$ [1]                                                    | -   | 0.83 | 1    | V             |
|             |                                         | $I_C = 4\text{ A}; I_B = 400\text{ mA}$ [1]                                                    | -   | 1.0  | 1.1  | V             |
| $V_{BEon}$  | base-emitter turn-on voltage            | $V_{CE} = 2\text{ V}; I_C = 2\text{ A}$                                                        | -   | 0.79 | 1    | V             |
| $t_d$       | delay time                              | $V_{CC} = 12.5\text{ V}; I_C = 3\text{ A}; I_{Bon} = 0.15\text{ A}; I_{Boff} = -0.15\text{ A}$ | -   | 12   | -    | ns            |
| $t_r$       | rise time                               |                                                                                                | -   | 36   | -    | ns            |
| $t_{on}$    | turn-on time                            |                                                                                                | -   | 48   | -    | ns            |
| $t_s$       | storage time                            |                                                                                                | -   | 230  | -    | ns            |
| $t_f$       | fall time                               |                                                                                                | -   | 50   | -    | ns            |
| $t_{off}$   | turn-off time                           |                                                                                                | -   | 280  | -    | ns            |
| $f_T$       | transition frequency                    | $V_{CE} = 10\text{ V}; I_C = 0.1\text{ A}; f = 100\text{ MHz}$                                 | -   | 100  | -    | MHz           |
| $C_C$       | collector capacitance                   | $V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$                               | -   | 60   | -    | pF            |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



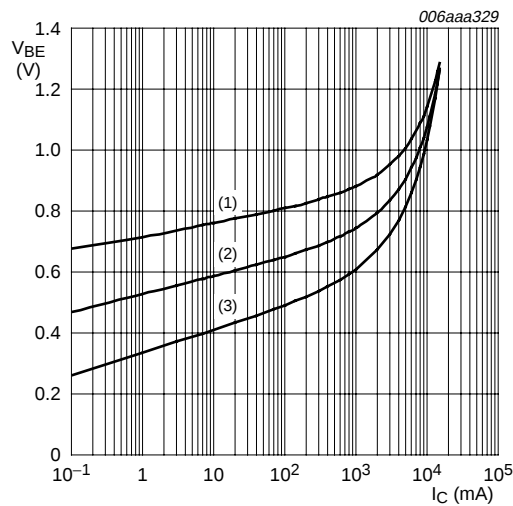
- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. DC current gain as a function of collector current; typical values



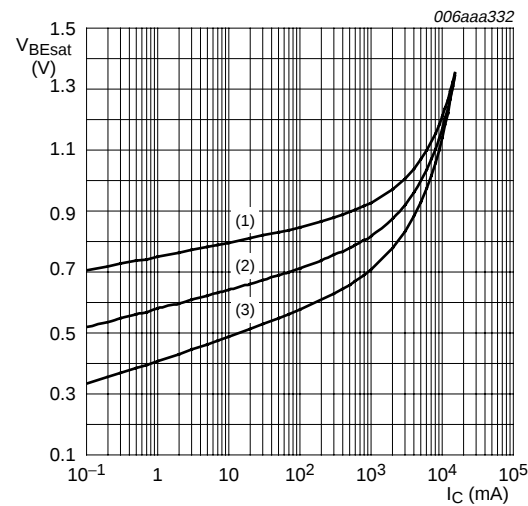
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 6. Collector current as a function of collector-emitter voltage; typical values



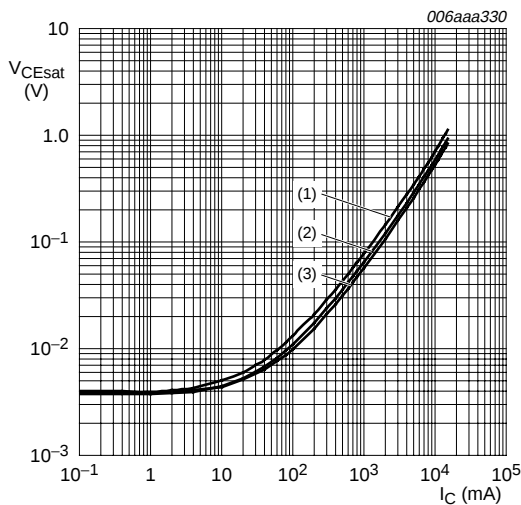
- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 7. Base-emitter voltage as a function of collector current; typical values



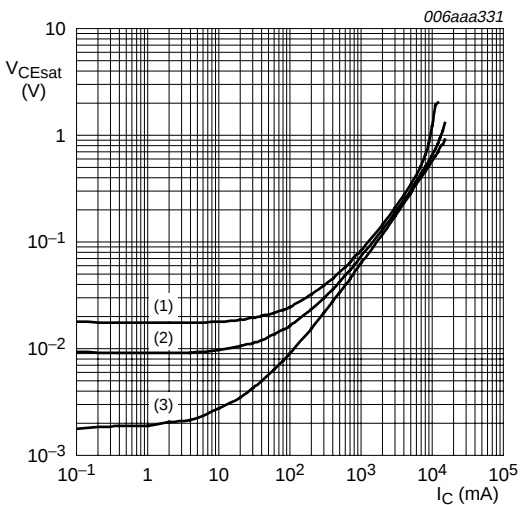
- $I_C/I_B = 20$
- (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



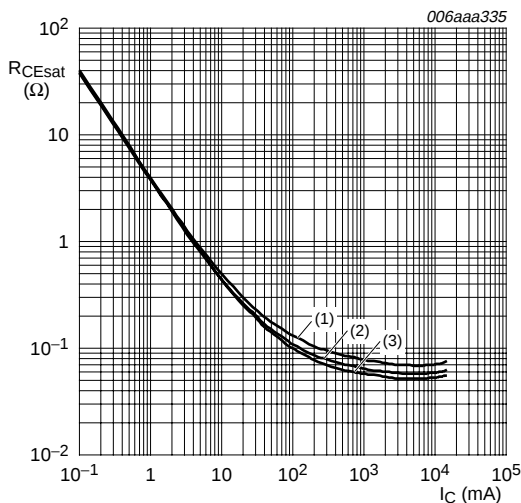
- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



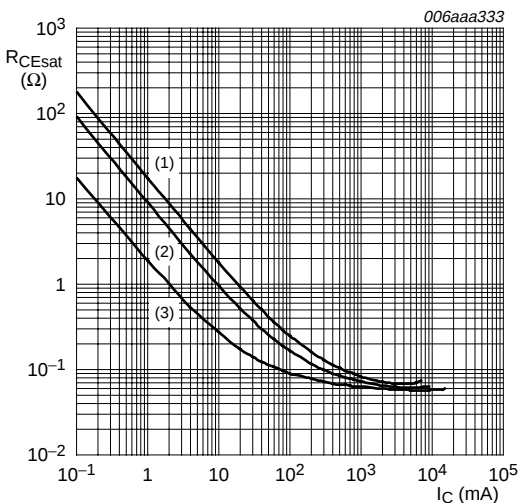
- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

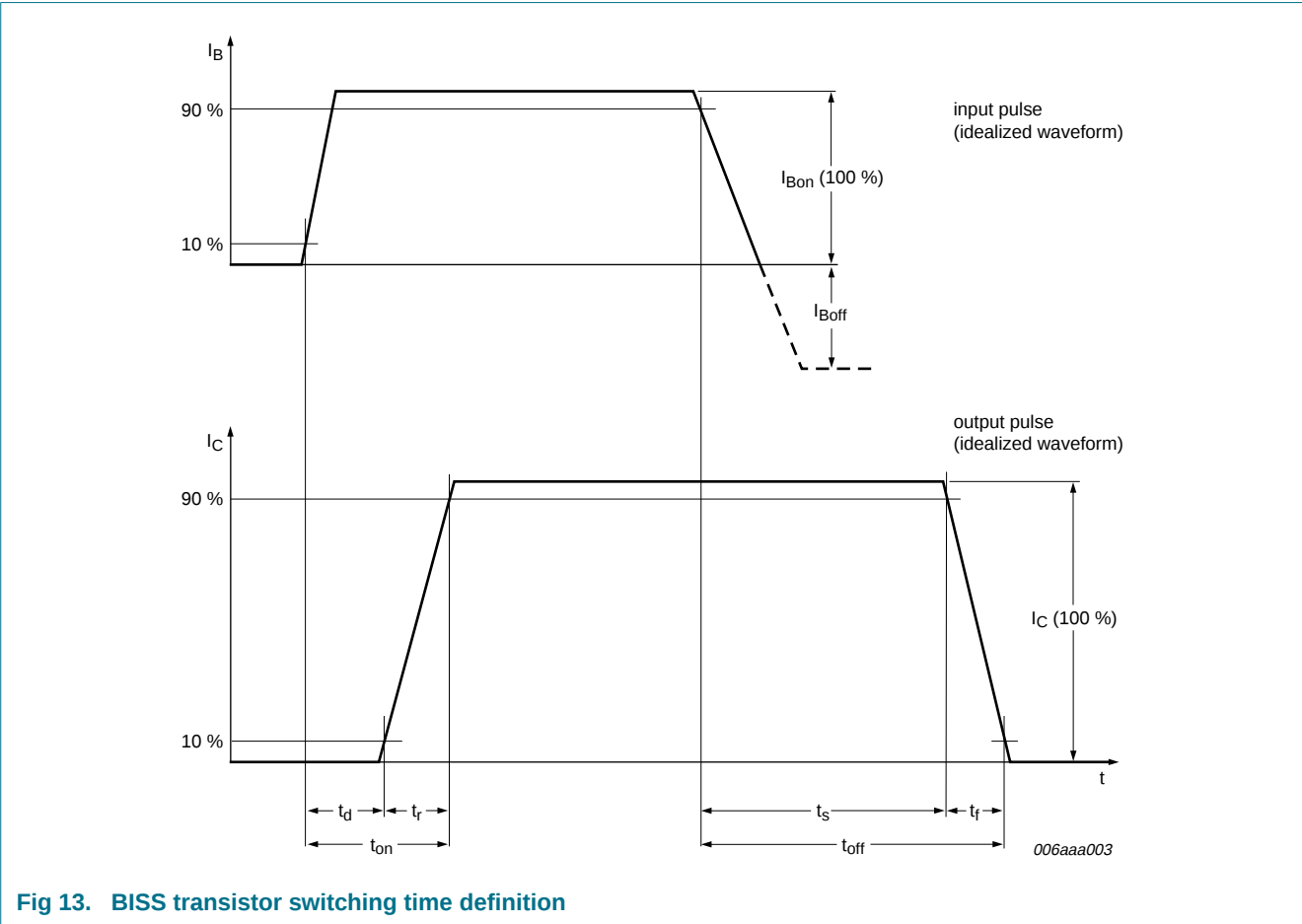


Fig 13. BISS transistor switching time definition

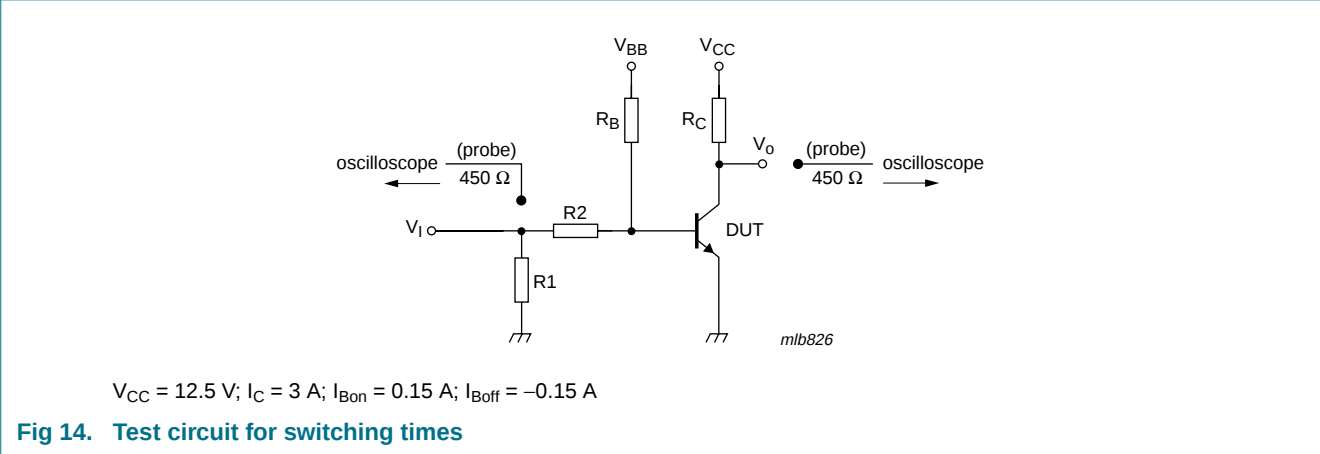
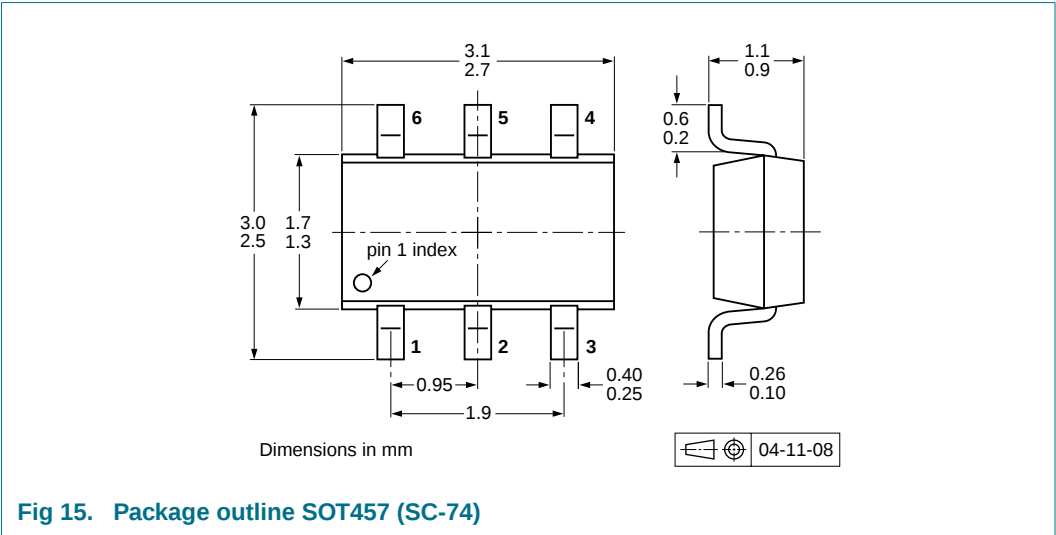


Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

**Table 8. Packing methods**

*The indicated -xxx are the last three digits of the 12NC ordering code.*[\[1\]](#)

| Type number | Package | Description                        | Packing quantity         |       |
|-------------|---------|------------------------------------|--------------------------|-------|
|             |         |                                    | 3000                     | 10000 |
| PBSS4420D   | SOT457  | 4 mm pitch, 8 mm tape and reel; T1 | <a href="#">[2]</a> -115 | -135  |
|             |         | 4 mm pitch, 8 mm tape and reel; T2 | <a href="#">[3]</a> -125 | -165  |

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering

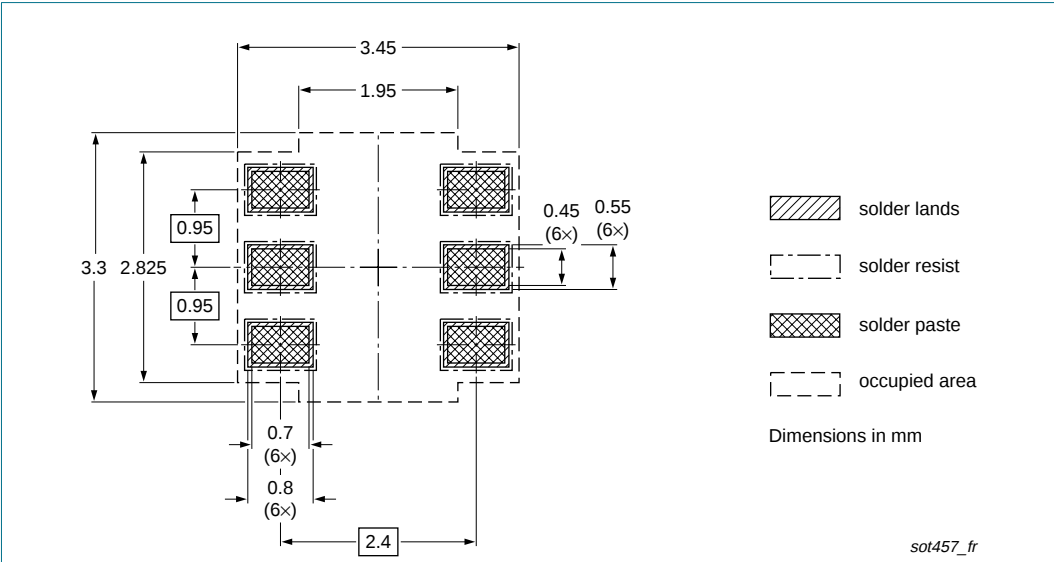


Fig 16. Reflow soldering footprint SOT457 (SC-74)

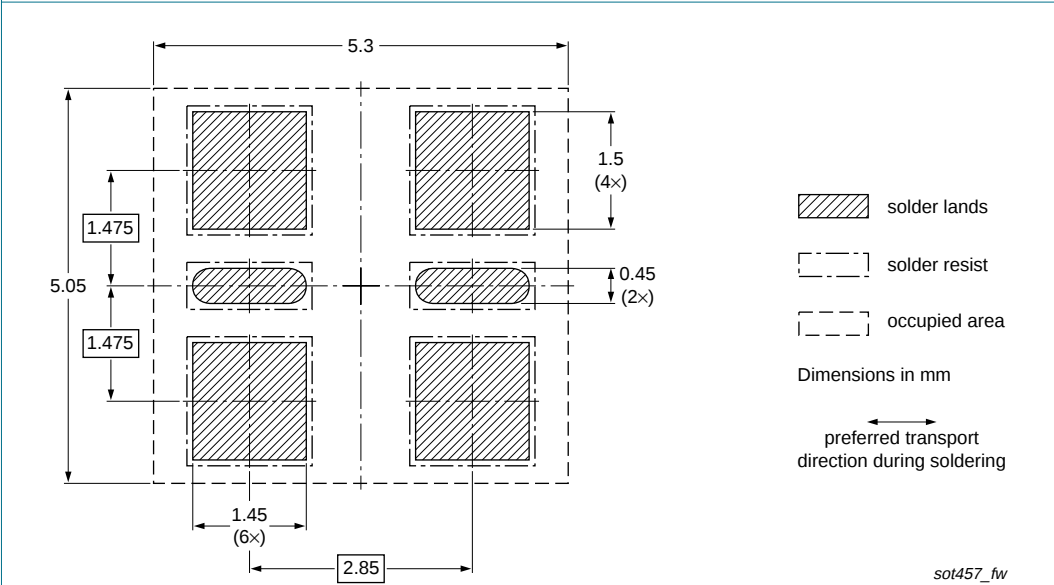


Fig 17. Wave soldering footprint SOT457 (SC-74)

## 12. Revision history

Table 9. Revision history

| Document ID    | Release date                                                                                                                                                                                                                                                                                                                                                                                                                   | Data sheet status  | Change notice | Supersedes  |
|----------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|---------------|-------------|
| PBSS4420D_2    | 20080924                                                                                                                                                                                                                                                                                                                                                                                                                       | Product data sheet | -             | PBSS4420D_1 |
| Modifications: | <ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• <a href="#">Figure 7</a>: amended</li><li>• <a href="#">Section 11 "Soldering"</a>: added</li><li>• <a href="#">Section 13 "Legal information"</a>: updated</li></ul> |                    |               |             |
| PBSS4420D_1    | 20050421                                                                                                                                                                                                                                                                                                                                                                                                                       | Product data sheet | -             | -           |

## 13. Legal information

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|-----------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 13.2 Definitions

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15. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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